

# MGFK38V2228

## 12.2~12.8GHz BAND 6W INTERNALLY MATCHED GaAs FET

### DESCRIPTION

The MGFK38V2228 is an internally impedance matched GaAs power FET especially designed for use in 12.2 ~ 12.8 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

### FEATURES

- Internally impedance matched
- High output power  
 $P_{1dB} = 6 \text{ W (TYP.) @ } f = 12.2 \sim 12.8 \text{ GHz}$
- High linear power gain  
 $G_{LP} = 6.0 \text{ dB (TYP.) @ } f = 12.2 \sim 12.8 \text{ GHz}$
- High power added efficiency  
 $\eta_{add} = 23\% \text{ (TYP.) @ } f = 12.2 \sim 12.8 \text{ GHz, } P_{1dB}$

### APPLICATION

For use in 12.2 ~ 12.8 GHz band amplifiers.

### QUALITY GRADE

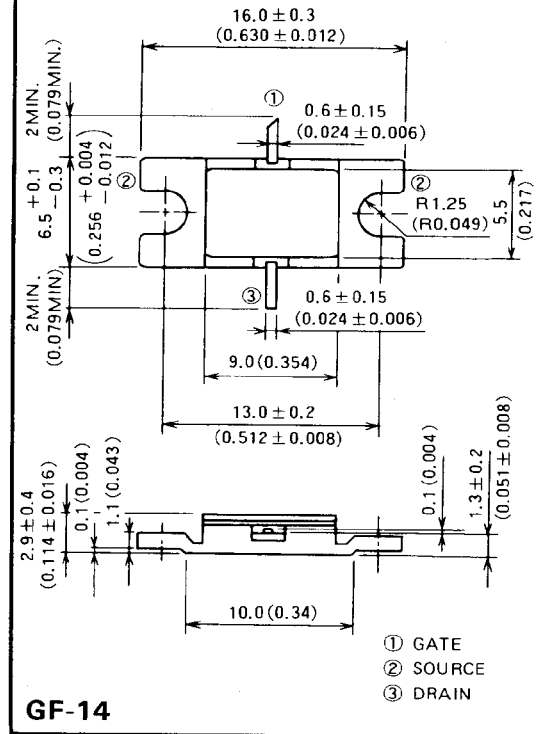
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### RECOMMENDED BIAS CONDITIONS

- $V_{DS} = 10\text{V}$
- $I_D = 2.4\text{A}$
- Refer to Bias Procedure

### OUTLINE DRAWING

Unit: millimeters (inches)



### ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

Symbol	Parameter	Rating	Unit
$V_{GDO}$	Gate to drain voltage	-15	V
$V_{GSO}$	Gate to source voltage	-15	V
$I_D$	Drain current	5.6	A
$I_{GR}$	Reverse gate current	-18	mA
$I_{GF}$	Forward gate current	36	mA
$P_T$	Total power dissipation *1	42.8	W
$T_{ch}$	Channel temperature	175	$^\circ\text{C}$
$T_{stg}$	Storage temperature	-65 ~ +175	$^\circ\text{C}$

\*1:  $T_c = 25^\circ\text{C}$

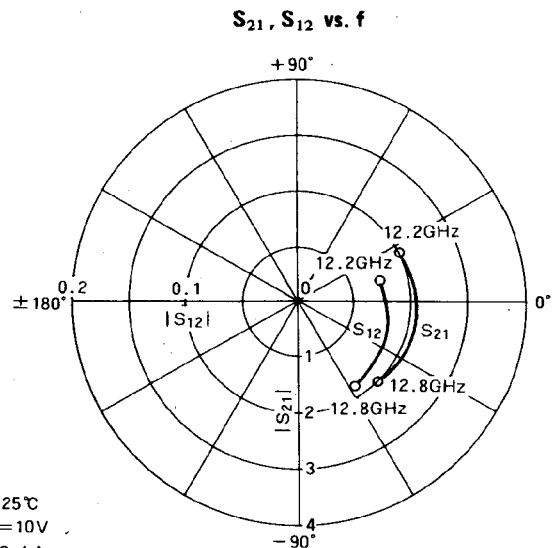
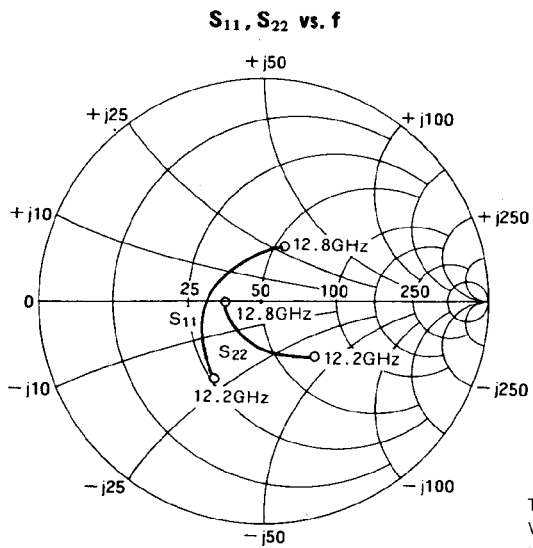
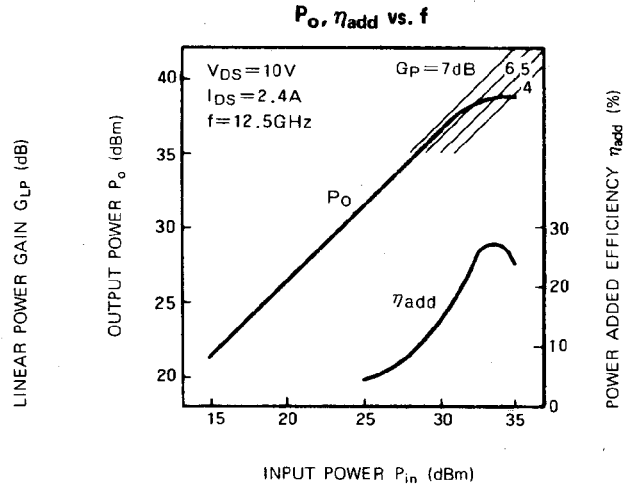
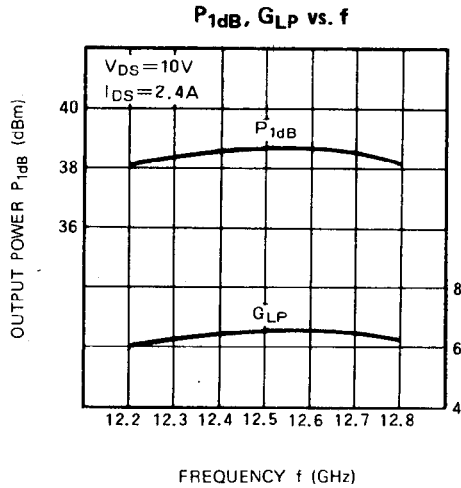
### ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$I_{DSS}$	Saturated drain current	$V_{DS} = 3\text{V, } V_{GS} = 0\text{V}$	—	4.0	5.6	A
$g_m$	Transconductance	$V_{DS} = 3\text{V, } I_D = 2.2\text{A}$	—	2.0	—	S
$V_{GS(off)}$	Gate to source cut-off voltage	$V_{DS} = 3\text{V, } I_D = 20\text{mA}$	-2	-3	-4	V
$P_{1dB}$	Output power at 1dB gain compression	$V_{DS} = 10\text{V, } I_D = 2.4\text{A, } f = 12.2 \sim 12.8\text{GHz}$	37	38	—	dBm
$G_{LP}$	Linear power gain		5.0	6.0	—	dB
$\eta_{add}$	Power added efficiency		—	23	—	%
$R_{th(ch-c)}$	Thermal resistance *1	$\Delta V_f$ method	—	—	3.5	$^\circ\text{C/W}$

\*1: Channel to case

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**TYPICAL CHARACTERISTICS** ( $T_a = 25^\circ\text{C}$ )



**S PARAMETERS** ( $T_a = 25^\circ\text{C}$ ,  $V_{DS} = 10\text{V}$ ,  $I_{DS} = 2.4\text{A}$ )

f (GHz)	S Parameters (TYP.)							
	$S_{11}$		$S_{21}$		$S_{12}$		$S_{22}$	
	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)
12.2	0.409	-124	1.97	27	0.074	18	0.324	-50
12.3	0.346	-144	2.05	16	0.076	7	0.279	-62
12.4	0.278	-170	2.14	4	0.078	-6	0.232	-79
12.5	0.245	165	2.14	-6	0.082	-18	0.188	-105
12.6	0.220	132	2.09	-19	0.083	-31	0.173	-135
12.7	0.234	101	2.06	-30	0.085	-42	0.176	-158
12.8	0.253	69	1.99	-43	0.092	-55	0.185	178